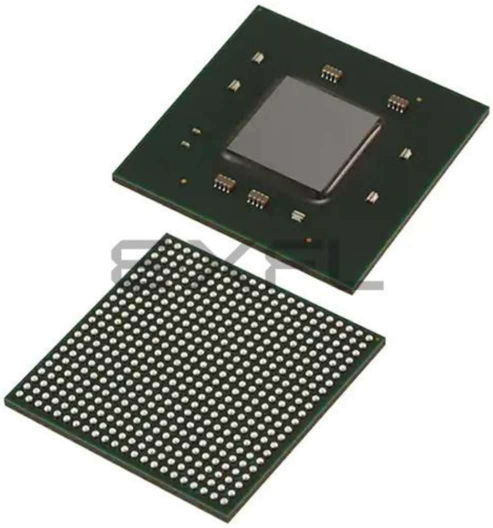
AMD Xilinx - XC7K70T-1FBG484I Datasheet



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The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Active
Number of LABs/CLBs	5125
Number of Logic Elements/Cells	65600
Total RAM Bits	4976640
Number of I/O	285
Number of Gates	-
Voltage - Supply	0.97V ~ 1.03V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	484-BBGA, FCBGA
Supplier Device Package	484-FCBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xc7k70t-1fbg484i

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Table 2: **Recommended Operating Conditions** [1] ***(Cont'd)***

Symbol	Description	Min	Typ	Max	Units
$V_{MGTAVTTRCAL}$[8]	Analog supply voltage for the resistor calibration circuit of the GTX transceiver column	1.17	1.2	1.23	V
XADC					
V_{CCADC}	XADC supply relative to GNDADC	1.71	1.80	1.89	V
V_{REFP}	Externally supplied reference voltage	1.20	1.25	1.30	V
Temperature					
T_j	Junction temperature operating range for commercial (C) temperature devices	0	–	85	°C
	Junction temperature operating range for extended (E) temperature devices	0	–	100	°C
	Junction temperature operating range for industrial (I) temperature devices	–40	–	100	°C

Notes:

1. All voltages are relative to ground.
2. V_{CCINT} and V_{CCBRAM} should be connected to the same supply.
3. Configuration data is retained even if V_{CCO} drops to 0V.
4. Includes V_{CCO} of 1.2V, 1.5V, 1.8V, 2.5V, and 3.3V.
5. The lower absolute voltage specification always applies.
6. A total of 200 mA per bank should not be exceeded.
7. V_{CCBATT} is required only when using bitstream encryption. If battery is not used, connect V_{CCBATT} to either ground or V_{CCAUX}.
8. Each voltage listed requires the filter circuit described in UG476: *7 Series FPGAs GTX/GTH Transceiver User Guide*.
9. For data rates ≤ 10.3125 Gb/s, $V_{MGTAVCC}$ should be 1.0V ±3% for lower power consumption.
10. For lower power consumption, $V_{MGTAVCC}$ should be 1.0V ±3% over the entire CPLL frequency range.

Table 3: **DC Characteristics Over Recommended Operating Conditions**

Symbol	Description	Min	Typ[1]	Max	Units
V_{DRINT}	Data retention V_{CCINT} voltage (below which configuration data might be lost)	0.75	–	–	V
V_{DRI}	Data retention V_{CCAUX} voltage (below which configuration data might be lost)	1.5	–	–	V
I_{REF}	V_{REF} leakage current per pin	–	–	15	µA
I_L	Input or output leakage current per pin (sample-tested)	–	–	15	µA
C_{IN}[2]	Die input capacitance at the pad	–	–	8	pF
I_{RPU}	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 3.3V	90	–	330	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 2.5V	68	–	250	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.8V	34	–	220	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.5V	23	–	150	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.2V	12	–	120	µA
I_{RPD}	Pad pull-down (when selected) @ V_{IN} = 3.3V	68	–	330	µA
	Pad pull-down (when selected) @ V_{IN} = 1.8V	45	–	180	µA
I_{CCADC}	Analog supply current, analog circuits in powered up state	–	–	25	mA
I_{BATT}[3]	Battery supply current	–	–	150	nA

Table 5: **Maximum Allowed AC Voltage Overshoot and Undershoot for 1.8V HP I/O Banks[1][2]** ***(Cont'd)***

AC Voltage Overshoot	% of UI @–40°C to 100°C	AC Voltage Undershoot	% of UI @–40°C to 100°C
V_{CCO} + 0.80	9.71	–0.80	50.0
V_{CCO} + 0.85	4.51	–0.85	28.4
V_{CCO} + 0.90	2.12	–0.90	12.7
V_{CCO} + 0.95	1.01	–0.95	5.79

Notes:

1. A total of 200 mA per bank should not be exceeded.
2. For UI smaller than 20 µs.

Table 6: **Typical Quiescent Supply Current**

Symbol	Description	Device	Speed Grade				Units
			1.0V			0.9V	
			-3	-2/-2L	-1	-2L	
I_{CCINTQ}	Quiescent V_{CCINT} supply current	XC7K70T	241	241	241	187	mA
		XC7K160T	474	474	474	368	mA
		XC7K325T	810	810	810	629	mA
		XC7K355T	993	993	993	771	mA
		XC7K410T	1080	1080	1080	838	mA
		XC7K420T	1313	1313	1313	1019	mA
		XC7K480T	1313	1313	1313	1019	mA
I_{CCOQ}	Quiescent V_{CCO} supply current	XC7K70T	1	1	1	1	mA
		XC7K160T	1	1	1	1	mA
		XC7K325T	1	1	1	1	mA
		XC7K355T	1	1	1	1	mA
		XC7K410T	1	1	1	1	mA
		XC7K420T	1	1	1	1	mA
		XC7K480T	1	1	1	1	mA
I_{CCAUXQ}	Quiescent V_{CCAUX} supply current	XC7K70T	21	21	21	21	mA
		XC7K160T	40	40	40	40	mA
		XC7K325T	68	68	68	68	mA
		XC7K355T	75	75	75	75	mA
		XC7K410T	85	85	85	85	mA
		XC7K420T	99	99	99	99	mA
		XC7K480T	99	99	99	99	mA
I_{CCAUX_IOQ}	Quiescent V_{CCAUX_IO} supply current	XC7K70T	N/A	N/A	N/A	N/A	mA
		XC7K160T	2	2	2	2	mA
		XC7K325T	2	2	2	2	mA
		XC7K355T	N/A	N/A	N/A	N/A	mA
		XC7K410T	2	2	2	2	mA
		XC7K420T	N/A	N/A	N/A	N/A	mA
		XC7K480T	N/A	N/A	N/A	N/A	mA

Table 6: **Typical Quiescent Supply Current *(Cont'd)***

Symbol	**Description**	**Device**	**Speed Grade**				**Units**
			1.0V			**0.9V**	
			-3	**-2/-2L**	**-1**	**-2L**	
$I_{CCBRAMQ}$	Quiescent V_{CCBRAM} supply current	XC7K70T	6	6	6	6	mA
		XC7K160T	14	14	14	14	mA
		XC7K325T	19	19	19	19	mA
		XC7K355T	31	31	31	31	mA
		XC7K410T	34	34	34	34	mA
		XC7K420T	41	41	41	41	mA
		XC7K480T	41	41	41	41	mA

Notes:

1. Typical values are specified at nominal voltage, 85°C junction temperatures (T_j) with single-ended SelectIO resources.
2. Typical values are for blank configured devices with no output current loads, no active input pull-up resistors, all I/O pins are 3-state and floating.
3. Use the XPower™ Estimator (XPE) spreadsheet tool (download at http://www.xilinx.com/power) to calculate static power consumption for conditions other than those specified.

Power-On/Off Power Supply Sequencing

The recommended power-on sequence is V_{CCINT}, V_{CCBRAM}, V_{CCAUX}, V_{CCAUX_IO}, and V_{CCO} to achieve minimum current draw and ensure that the I/Os are 3-stated at power-on. The recommended power-off sequence is the reverse of the power-on sequence. If V_{CCINT} and V_{CCBRAM} have the same recommended voltage levels then both can be powered by the same supply and ramped simultaneously. If V_{CCAUX}, V_{CCAUX_IO}, and V_{CCO} have the same recommended voltage levels then they can be powered by the same supply and ramped simultaneously.

For V_{CCO} voltages of 3.3V in HR I/O banks and configuration bank 0:

- The voltage difference between V_{CCO} and V_{CCAUX} must not exceed 2.625V for longer than $T_{VCCO2VCCAUX}$ for each power-on/off cycle to maintain device reliability levels.
- The $T_{VCCO2VCCAUX}$ time can be allocated in any percentage between the power-on and power-off ramps.

The recommended power-on sequence to achieve minimum current draw for the GTX transceivers is V_{CCINT}, $V_{MGTAVCC}$, $V_{MGTAVTT}$ OR $V_{MGTAVCC}$, V_{CCINT}, $V_{MGTAVTT}$. There is no recommended sequencing for $V_{MGTVCCAUX}$. Both $V_{MGTAVCC}$ and V_{CCINT} can be ramped simultaneously. The recommended power-off sequence is the reverse of the power-on sequence to achieve minimum current draw.

If these recommended sequences are not met, current drawn from $V_{MGTAVTT}$ can be higher than specifications during power-up and power-down.

- When $V_{MGTAVTT}$ is powered before $V_{MGTAVCC}$ and $V_{MGTAVTT} – V_{MGTAVCC} > 150$ mV and $V_{MGTAVCC} < 0.7V$, the $V_{MGTAVTT}$ current draw can increase by 460 mA per transceiver during $V_{MGTAVCC}$ ramp up. The duration of the current draw can be up to 0.3 x $T_{MGTAVCC}$ (ramp time from GND to 90% of $V_{MGTAVCC}$). The reverse is true for power-down.
- When $V_{MGTAVTT}$ is powered before V_{CCINT} and $V_{MGTAVTT} – V_{CCINT} > 150$ mV and $V_{CCINT} < 0.7V$, the $V_{MGTAVTT}$ current draw can increase by 50 mA per transceiver during V_{CCINT} ramp up. The duration of the current draw can be up to 0.3 x T_{VCCINT} (ramp time from GND to 90% of V_{CCINT}). The reverse is true for power-down.

Table 7 shows the minimum current, in addition to I_{CCQ}, that are required by Kintex-7 devices for proper power-on and configuration. If the current minimums shown in Table 6 and Table 7 are met, the device powers on after all five supplies have passed through their power-on reset threshold voltages. The FPGA must not be configured until after V_{CCINT} is applied.

Once initialized and configured, use the XPower tools to estimate current drain on these supplies.

Table 7: **Power-On Current for Kintex-7 Devices**

Device	$I_{CCINTMIN}$	$I_{CCAUXMIN}$	I_{CCOMIN}	I_{CCAUX_IOMIN}	$I_{CCBRAMMIN}$	Units
	Typ[(1)]	Typ[(1)]	Typ[(1)]	Typ[(1)]	Typ[(1)]	
XC7K70T	I_{CCINTQ} + 450	I_{CCAUXQ} + 40	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 40 mA per bank	$I_{CCBRAMQ}$ + 40	mA
XC7K160T	I_{CCINTQ} + 550	I_{CCAUXQ} + 50	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 40 mA per bank	$I_{CCBRAMQ}$ + 40	mA
XC7K325T	I_{CCINTQ} + 600	I_{CCAUXQ} + 80	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 40 mA per bank	$I_{CCBRAMQ}$ + 40	mA
XC7K355T	I_{CCINTQ} + 1450	I_{CCAUXQ} + 109	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 40 mA per bank	$I_{CCBRAMQ}$ + 81	mA
XC7K410T	I_{CCINTQ} + 1500	I_{CCAUXQ} + 125	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 40 mA per bank	$I_{CCBRAMQ}$ + 90	mA
XC7K420T	I_{CCINTQ} + 2200	I_{CCAUXQ} + 180	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 40 mA per bank	$I_{CCBRAMQ}$ + 108	mA
XC7K480T	I_{CCINTQ} + 2200	I_{CCAUXQ} + 180	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 40 mA per bank	$I_{CCBRAMQ}$ + 108	mA

Notes:

1. Typical values are specified at nominal voltage, 25°C.
2. Use the XPower Estimator (XPE) spreadsheet tool (download at http://www.xilinx.com/power) to calculate maximum power-on currents.

Table 8: **Power Supply Ramp Time**

Symbol	Description	Conditions	Min	Max	Units
T_{VCCINT}	Ramp time from GND to 90% of V_{CCINT}		0.2	50	ms
T_{VCCO}	Ramp time from GND to 90% of V_{CCO}		0.2	50	ms
T_{VCCAUX}	Ramp time from GND to 90% of V_{CCAUX}		0.2	50	ms
T_{VCCAUX_IO}	Ramp time from GND to 90% of V_{CCAUX_IO}		0.2	50	ms
$T_{VCCBRAM}$	Ramp time from GND to 90% of V_{CCBRAM}		0.2	50	ms
$T_{VCCO2VCCAUX}$	Allowed time per power cycle for $V_{CCO} - V_{CCAUX} > 2.625V$	$T_J = 100°C$[(1)]	–	500	ms
		$T_J = 85°C$[(1)]	–	800	
$T_{MGTAVCC}$	Ramp time from GND to 90% of $V_{MGTAVCC}$		0.2	50	ms
$T_{MGTAVTT}$	Ramp time from GND to 90% of $V_{MGTAVTT}$		0.2	50	ms
$T_{MGTVCCAUX}$	Ramp time from GND to 90% of $V_{MGTVCCAUX}$		0.2	50	ms

Notes:

1. Based on 240,000 power cycles with nominal V_{CCO} of 3.3V or 36,500 power cycles with a worst case V_{CCO} of 3.465V.

DC Input and Output Levels

Values for V_{IL} and V_{IH} are recommended input voltages. Values for I_{OL} and I_{OH} are guaranteed over the recommended operating conditions at the V_{OL} and V_{OH} test points. Only selected standards are tested. These are chosen to ensure that all standards meet their specifications. The selected standards are tested at a minimum V_{CCO} with the respective V_{OL} and V_{OH} voltage levels shown. Other standards are sample tested.

Table 9: **SelectIO DC Input and Output Levels (1)(2)**

I/O Standard	V_{IL}		V_{IH}		V_{OL}	V_{OH}	I_{OL}	I_{OH}
	V, Min	V, Max	V, Min	V, Max	V, Max	V, Min	mA	mA
HSTL_I	–0.300	$V_{REF} - 0.100$	$V_{REF} + 0.100$	$V_{CCO} + 0.300$	0.400	$V_{CCO} - 0.400$	8	–8
HSTL_I_12	–0.300	$V_{REF} - 0.080$	$V_{REF} + 0.080$	$V_{CCO} + 0.300$	25% V_{CCO}	75% V_{CCO}	6.3	–6.3
HSTL_I_18	–0.300	$V_{REF} - 0.100$	$V_{REF} + 0.100$	$V_{CCO} + 0.300$	0.400	$V_{CCO} - 0.400$	8	–8
HSTL_II	–0.300	$V_{REF} - 0.100$	$V_{REF} + 0.100$	$V_{CCO} + 0.300$	0.400	$V_{CCO} - 0.400$	16	–16
HSTL_II_18	–0.300	$V_{REF} - 0.100$	$V_{REF} + 0.100$	$V_{CCO} + 0.300$	0.400	$V_{CCO} - 0.400$	16	–16
HSUL_12	–0.300	$V_{REF} - 0.130$	$V_{REF} + 0.130$	$V_{CCO} + 0.300$	20% V_{CCO}	80% V_{CCO}	0.1	–0.1
LVCMOS12	–0.300	35% V_{CCO}	65% V_{CCO}	$V_{CCO} + 0.300$	0.400	$V_{CCO} - 0.400$	Note 3	Note 3
LVCMOS15, LVDCI_15	–0.300	35% V_{CCO}	65% V_{CCO}	$V_{CCO} + 0.300$	25% V_{CCO}	75% V_{CCO}	Note 4	Note 4
LVCMOS18, LVDCI_18	–0.300	35% V_{CCO}	65% V_{CCO}	$V_{CCO} + 0.300$	0.450	$V_{CCO} - 0.450$	Note 5	Note 5
LVCMOS25	–0.300	0.700	1.700	$V_{CCO} + 0.300$	0.400	$V_{CCO} - 0.400$	Note 6	Note 6
LVCMOS33	–0.300	0.800	2.000	3.450	0.400	$V_{CCO} - 0.400$	Note 6	Note 6
LVTTL	–0.300	0.800	2.000	3.450	0.400	2.400	Note 7	Note 7
MOBILE_DDR	–0.300	20% V_{CCO}	80% V_{CCO}	$V_{CCO} + 0.300$	10% V_{CCO}	90% V_{CCO}	0.1	–0.1
PCI33_3	–0.500	30% V_{CCO}	50% V_{CCO}	$V_{CCO} + 0.500$	10% V_{CCO}	90% V_{CCO}	1.5	–0.5
SSTL12	–0.300	$V_{REF} - 0.100$	$V_{REF} + 0.100$	$V_{CCO} + 0.300$	$V_{CCO}/2 - 0.150$	$V_{CCO}/2 + 0.150$	14.25	–14.25
SSTL135	–0.300	$V_{REF} - 0.090$	$V_{REF} + 0.090$	$V_{CCO} + 0.300$	$V_{CCO}/2 - 0.150$	$V_{CCO}/2 + 0.150$	13.0	–13.0
SSTL135_R	–0.300	$V_{REF} - 0.090$	$V_{REF} + 0.090$	$V_{CCO} + 0.300$	$V_{CCO}/2 - 0.150$	$V_{CCO}/2 + 0.150$	8.9	–8.9
SSTL15	–0.300	$V_{REF} - 0.100$	$V_{REF} + 0.100$	$V_{CCO} + 0.300$	$V_{CCO}/2 - 0.175$	$V_{CCO}/2 + 0.175$	13.0	–13.0
SSTL15_R	–0.300	$V_{REF} - 0.100$	$V_{REF} + 0.100$	$V_{CCO} + 0.300$	$V_{CCO}/2 - 0.175$	$V_{CCO}/2 + 0.175$	8.9	–8.9
SSTL18_I	–0.300	$V_{REF} - 0.125$	$V_{REF} + 0.125$	$V_{CCO} + 0.300$	$V_{CCO}/2 - 0.470$	$V_{CCO}/2 + 0.470$	8	–8
SSTL18_II	–0.300	$V_{REF} - 0.125$	$V_{REF} + 0.125$	$V_{CCO} + 0.300$	$V_{CCO}/2 - 0.600$	$V_{CCO}/2 + 0.600$	13.4	–13.4

Notes:

1. Tested according to relevant specifications.
2. 3.3V and 2.5V standards are only supported in 3.3V I/O banks.
3. Supported drive strengths of 2, 4, 6, or 8 mA in HP I/O banks and 4, 8, or 12 mA in HR I/O banks.
4. Supported drive strengths of 2, 4, 6, 8, 12, or 16 mA in HP I/O banks and 4, 8, 12, or 16 mA in HR I/O banks.
5. Supported drive strengths of 2, 4, 6, 8, 12, or 16 mA in HP I/O banks and 4, 8, 12, 16, or 24 mA in HR I/O banks.
6. Supported drive strengths of 4, 8, 12, or 16 mA
7. Supported drive strengths of 4, 8, 12, 16, or 24 mA
8. For detailed interface specific DC voltage levels, see UG471: *7 Series FPGAs SelectIO Resources User Guide*.

AC Switching Characteristics

All values represented in this data sheet are based on the speed specifications in ISE® software 14.3 v1.07 for the -3, -2, -2L(1.0V), -1, and v1.06 for -2L(0.9V) speed grades.

Switching characteristics are specified on a per-speed-grade basis and can be designated as Advance, Preliminary, or Production. Each designation is defined as follows:

Advance Product Specification

These specifications are based on simulations only and are typically available soon after device design specifications are frozen. Although speed grades with this designation are considered relatively stable and conservative, some under-reporting might still occur.

Preliminary Product Specification

These specifications are based on complete ES (engineering sample) silicon characterization. Devices and speed grades with this designation are intended to give a better indication of the expected performance of production silicon. The probability of under-reporting delays is greatly reduced as compared to Advance data.

Product Specification

These specifications are released once enough production silicon of a particular device family member has been characterized to provide full correlation between specifications and devices over numerous production lots. There is no under-reporting of delays, and customers receive formal notification of any subsequent changes. Typically, the slowest speed grades transition to production before faster speed grades.

Testing of AC Switching Characteristics

Internal timing parameters are derived from measuring internal test patterns. All AC switching characteristics are representative of worst-case supply voltage and junction temperature conditions.

For more specific, more precise, and worst-case guaranteed data, use the values reported by the static timing analyzer and back-annotate to the simulation net list. Unless otherwise noted, values apply to all Kintex-7 FPGAs.

Speed Grade Designations

Since individual family members are produced at different times, the migration from one category to another depends completely on the status of the fabrication process for each device. Table 14 correlates the current status of each Kintex-7 device on a per speed grade basis.

Table 14: **Kintex-7 Device Speed Grade Designations**

Device	Speed Grade Designations		
	Advance	Preliminary	Production
XC7K70T			-3, -2, -2L(1.0V), -1, and -2L (0.9V)
XC7K160T			-3, -2, -2L(1.0V), -1, and -2L (0.9V)
XC7K325T			-3, -2, -2L(1.0V), -1, and -2L (0.9V)
XC7K355T			-3, -2, -2L(1.0V), -1, and -2L (0.9V)
XC7K410T			-3, -2, -2L(1.0V), -1, and -2L (0.9V)
XC7K420T			-3, -2, -2L(1.0V), -1, and -2L (0.9V)
XC7K480T			-3, -2, -2L(1.0V), -1, and -2L (0.9V)

IOB Pad Input/Output/3-State

Table 19 (3.3V high-range IOB (HR)) and Table 20 (1.8V high-performance IOB (HP)) summarizes the values of standard-specific data input delay adjustments, output delays terminating at pads (based on standard) and 3-state delays.

- T_{IOPI} is described as the delay from IOB pad through the input buffer to the I-pin of an IOB pad. The delay varies depending on the capability of the SelectIO input buffer.
- T_{IOOP} is described as the delay from the O pin to the IOB pad through the output buffer of an IOB pad. The delay varies depending on the capability of the SelectIO output buffer.
- T_{IOTP} is described as the delay from the T pin to the IOB pad through the output buffer of an IOB pad, when 3-state is disabled. The delay varies depending on the SelectIO capability of the output buffer. In HP I/O banks, the internal DCI termination turn-on time is always faster than T_{IOTP} when the DCITERMDISABLE pin is used. In HR I/O banks, the IN_TERM termination turn-on time is always faster than T_{IOTP} when the INTERMDISABLE pin is used.

Table 19: **3.3V IOB High Range (HR) Switching Characteristics**

I/O Standard	T_{IOPI}				T_{IOOP}				T_{IOTP}				Units
	Speed Grade				Speed Grade				Speed Grade				
	1.0V			0.9V	1.0V			0.9V	1.0V			0.9V	
	-3	-2/-2L	-1	-2L	-3	-2/-2L	-1	-2L	-3	-2/-2L	-1	-2L	
LVTTL_S4	1.31	1.42	1.64	1.51	5.27	5.63	6.05	4.13	6.03	6.49	7.04	4.64	ns
LVTTL_S8	1.31	1.42	1.64	1.51	4.45	4.83	5.30	3.86	5.21	5.69	6.29	4.38	ns
LVTTL_S12	1.31	1.42	1.64	1.51	4.45	4.83	5.29	3.84	5.21	5.69	6.28	4.36	ns
LVTTL_S16	1.31	1.42	1.64	1.51	3.47	3.88	4.40	3.39	4.23	4.74	5.39	3.91	ns
LVTTL_S24	1.31	1.42	1.64	1.51	3.58	3.99	4.51	3.61	4.34	4.85	5.50	4.13	ns
LVTTL_F4	1.31	1.42	1.64	1.51	4.70	4.98	5.29	3.58	5.46	5.84	6.28	4.09	ns
LVTTL_F8	1.31	1.42	1.64	1.51	3.66	4.06	4.56	3.06	4.42	4.92	5.55	3.58	ns
LVTTL_F12	1.31	1.42	1.64	1.51	3.66	4.06	4.56	3.05	4.42	4.92	5.55	3.56	ns
LVTTL_F16	1.31	1.42	1.64	1.51	2.57	2.85	3.15	2.88	3.33	3.71	4.14	3.39	ns
LVTTL_F24	1.31	1.42	1.64	1.51	2.41	2.64	2.89	2.94	3.17	3.50	3.88	3.45	ns
LVDS_25(1)	0.64	0.68	0.80	0.83	1.36	1.47	1.55	1.58	2.12	2.33	2.54	2.09	ns
MINI_LVDS_25	0.68	0.70	0.79	0.83	1.36	1.47	1.55	1.59	2.12	2.33	2.54	2.11	ns
BLVDS_25(1)	0.65	0.69	0.80	0.83	1.83	2.02	2.20	2.16	2.59	2.88	3.19	2.67	ns
RSDS_25 (point to point)(1)	0.63	0.68	0.79	0.83	1.36	1.48	1.55	1.59	2.12	2.34	2.54	2.11	ns
PPDS_25(1)	0.65	0.69	0.80	0.83	1.36	1.49	1.58	1.59	2.12	2.35	2.57	2.11	ns
TMDS_33(1)	0.72	0.76	0.86	0.83	1.43	1.54	1.60	1.70	2.19	2.40	2.59	2.22	ns
PCI33_3(1)	1.28	1.41	1.65	1.50	2.71	3.08	3.52	3.42	3.47	3.94	4.51	3.94	ns
HSUL_12	0.63	0.64	0.71	0.79	2.06	2.31	2.59	2.13	2.82	3.17	3.58	2.64	ns
DIFF_HSUL_12	0.58	0.61	0.70	0.81	1.83	2.04	2.26	1.92	2.59	2.90	3.25	2.44	ns
HSTL_I_S	0.61	0.64	0.73	0.79	1.55	1.69	1.80	1.91	2.31	2.55	2.79	2.42	ns
HSTL_II_S	0.61	0.64	0.73	0.78	1.21	1.34	1.43	1.70	1.97	2.20	2.42	2.22	ns
HSTL_I_18_S	0.64	0.67	0.76	0.79	1.28	1.39	1.45	1.58	2.04	2.25	2.44	2.09	ns
HSTL_II_18_S	0.64	0.67	0.76	0.79	1.18	1.31	1.40	1.69	1.94	2.17	2.39	2.20	ns
DIFF_HSTL_I_S	0.63	0.67	0.77	0.78	1.42	1.54	1.61	1.84	2.18	2.40	2.60	2.36	ns
DIFF_HSTL_II_S	0.63	0.67	0.77	0.79	1.15	1.24	1.27	1.78	1.91	2.10	2.26	2.30	ns
DIFF_HSTL_I_18_S	0.65	0.69	0.78	0.79	1.27	1.38	1.43	1.67	2.03	2.24	2.42	2.19	ns
DIFF_HSTL_II_18_S	0.65	0.69	0.78	0.81	1.14	1.23	1.26	1.72	1.90	2.09	2.25	2.23	ns

Table 19: **3.3V IOB High Range (HR) Switching Characteristics *(Cont'd)***

I/O Standard	T_{IOPI}				T_{IOOP}				T_{IOTP}				Units
	Speed Grade				Speed Grade				Speed Grade				
	1.0V			0.9V	1.0V			0.9V	1.0V			0.9V	
	-3	-2/-2L	-1	-2L	-3	-2/-2L	-1	-2L	-3	-2/-2L	-1	-2L	
HSTL_I_F	0.61	0.64	0.73	0.79	1.10	1.19	1.23	1.41	1.86	2.05	2.22	1.92	ns
HSTL_II_F	0.61	0.64	0.73	0.78	1.05	1.18	1.28	1.42	1.81	2.04	2.27	1.94	ns
HSTL_I_18_F	0.64	0.67	0.76	0.79	1.05	1.18	1.28	1.44	1.81	2.04	2.27	1.95	ns
HSTL_II_18_F	0.64	0.67	0.76	0.79	1.03	1.14	1.23	1.42	1.79	2.00	2.22	1.94	ns
DIFF_HSTL_I_F	0.63	0.67	0.77	0.78	1.09	1.18	1.22	1.48	1.85	2.04	2.21	2.00	ns
DIFF_HSTL_II_F	0.63	0.67	0.77	0.79	1.02	1.11	1.14	1.48	1.78	1.97	2.13	2.00	ns
DIFF_HSTL_I_18_F	0.65	0.69	0.78	0.79	1.08	1.17	1.21	1.48	1.84	2.03	2.20	2.00	ns
DIFF_HSTL_II_18_F	0.65	0.69	0.78	0.81	1.01	1.10	1.13	1.48	1.77	1.96	2.12	2.00	ns
LVCMOS33_S4	1.31	1.40	1.60	1.54	5.23	5.61	6.09	4.13	5.99	6.47	7.08	4.64	ns
LVCMOS33_S8	1.31	1.40	1.60	1.54	4.46	4.85	5.33	3.84	5.22	5.71	6.32	4.36	ns
LVCMOS33_S12	1.31	1.40	1.60	1.54	3.46	3.89	4.42	3.41	4.22	4.75	5.41	3.92	ns
LVCMOS33_S16	1.31	1.40	1.60	1.54	3.06	3.43	3.88	3.72	3.82	4.29	4.87	4.23	ns
LVCMOS33_F4	1.31	1.40	1.60	1.54	4.70	5.01	5.36	3.58	5.46	5.87	6.35	4.09	ns
LVCMOS33_F8	1.31	1.40	1.60	1.54	3.62	4.04	4.56	3.06	4.38	4.90	5.55	3.58	ns
LVCMOS33_F12	1.31	1.40	1.60	1.54	2.57	2.85	3.15	2.88	3.33	3.71	4.14	3.39	ns
LVCMOS33_F16	1.31	1.40	1.60	1.54	2.44	2.69	2.96	2.88	3.20	3.55	3.95	3.39	ns
LVCMOS25_S4	1.08	1.16	1.32	1.36	4.49	4.80	5.16	3.44	5.25	5.66	6.15	3.95	ns
LVCMOS25_S8	1.08	1.16	1.32	1.36	3.66	4.04	4.49	3.20	4.42	4.90	5.48	3.72	ns
LVCMOS25_S12	1.08	1.16	1.32	1.36	2.77	3.10	3.49	2.80	3.53	3.96	4.48	3.31	ns
LVCMOS25_S16	1.08	1.16	1.32	1.36	3.24	3.62	4.09	3.14	4.00	4.48	5.08	3.66	ns
LVCMOS25_F4	1.08	1.16	1.32	1.36	3.96	4.31	4.72	3.06	4.72	5.17	5.71	3.58	ns
LVCMOS25_F8	1.08	1.16	1.32	1.36	2.43	2.87	3.42	2.50	3.19	3.73	4.41	3.02	ns
LVCMOS25_F12	1.08	1.16	1.32	1.36	2.23	2.63	3.13	2.48	2.99	3.49	4.12	3.00	ns
LVCMOS25_F16	1.08	1.16	1.32	1.36	1.92	2.17	2.45	2.33	2.68	3.03	3.44	2.84	ns
LVCMOS18_S4	0.64	0.66	0.74	0.87	3.24	3.45	3.66	1.91	4.00	4.31	4.65	2.42	ns
LVCMOS18_S8	0.64	0.66	0.74	0.87	2.58	2.91	3.31	2.50	3.34	3.77	4.30	3.02	ns
LVCMOS18_S12	0.64	0.66	0.74	0.87	2.58	2.91	3.31	2.50	3.34	3.77	4.30	3.02	ns
LVCMOS18_S16	0.64	0.66	0.74	0.87	1.82	2.03	2.24	1.84	2.58	2.89	3.23	2.36	ns
LVCMOS18_S24(1)	0.64	0.66	0.74	0.87	1.74	1.92	2.08	1.92	2.50	2.78	3.07	2.44	ns
LVCMOS18_F4	0.64	0.66	0.74	0.87	3.12	3.31	3.49	1.77	3.88	4.17	4.48	2.28	ns
LVCMOS18_F8	0.64	0.66	0.74	0.87	1.91	2.13	2.36	2.00	2.67	2.99	3.35	2.52	ns
LVCMOS18_F12	0.64	0.66	0.74	0.87	1.91	2.13	2.36	2.00	2.67	2.99	3.35	2.52	ns
LVCMOS18_F16	0.64	0.66	0.74	0.87	1.52	1.68	1.81	1.72	2.28	2.54	2.80	2.23	ns
LVCMOS18_F24(1)	0.64	0.66	0.74	0.87	1.34	1.46	1.55	1.66	2.10	2.32	2.54	2.17	ns
LVCMOS15_S4	0.66	0.69	0.81	0.90	3.48	3.74	4.03	2.22	4.24	4.60	5.02	2.73	ns
LVCMOS15_S8	0.66	0.69	0.81	0.90	2.37	2.67	3.01	2.41	3.13	3.53	4.00	2.92	ns
LVCMOS15_S12	0.66	0.69	0.81	0.90	1.83	2.03	2.23	1.91	2.59	2.89	3.22	2.42	ns

Table 21 specifies the values of T_{IOTPHZ} and $T_{IOIBUFDISABLE}$. T_{IOTPHZ} is described as the delay from the T pin to the IOB pad through the output buffer of an IOB pad, when 3-state is enabled (i.e., a high impedance state). $T_{IOIBUFDISABLE}$ is described as the IOB delay from IBUFDISABLE to O output. In HP I/O banks, the internal DCI termination turn-off time is always faster than T_{IOTPHZ} when the DCITERMDISABLE pin is used. In HR I/O banks, the internal IN_TERM termination turn-off time is always faster than T_{IOTPHZ} when the INTERMDISABLE pin is used.

Table 21: **IOB 3-state Output Switching Characteristics**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
T_{IOTPHZ}	T input to pad high-impedance	0.76	0.86	0.99	0.62	ns
$T_{IOIBUFDISABLE\_HR}$	IBUF turn-on time from IBUFDISABLE to O output for HR I/O banks	1.72	1.89	2.14	2.17	ns
$T_{IOIBUFDISABLE\_HP}$	IBUF turn-on time from IBUFDISABLE to O output for HP I/O banks	1.31	1.46	1.76	1.86	ns

CLB Switching Characteristics

Table 28: **CLB Switching Characteristics**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
Combinatorial Delays						
T_{ILO}	An – Dn LUT address to A	0.05	0.05	0.06	0.07	ns, Max
T_{ILO_2}	An – Dn LUT address to AMUX/CMUX	0.15	0.16	0.19	0.22	ns, Max
T_{ILO_3}	An – Dn LUT address to BMUX_A	0.24	0.25	0.30	0.37	ns, Max
T_{ITO}	An – Dn inputs to A – D Q outputs	0.58	0.61	0.74	0.91	ns, Max
T_{AXA}	AX inputs to AMUX output	0.38	0.40	0.49	0.62	ns, Max
T_{AXB}	AX inputs to BMUX output	0.40	0.42	0.52	0.66	ns, Max
T_{AXC}	AX inputs to CMUX output	0.39	0.41	0.50	0.62	ns, Max
T_{AXD}	AX inputs to DMUX output	0.43	0.44	0.52	0.67	ns, Max
T_{BXB}	BX inputs to BMUX output	0.31	0.33	0.40	0.51	ns, Max
T_{BXD}	BX inputs to DMUX output	0.38	0.39	0.47	0.62	ns, Max
T_{CXC}	CX inputs to CMUX output	0.27	0.28	0.34	0.43	ns, Max
T_{CXD}	CX inputs to DMUX output	0.33	0.34	0.41	0.54	ns, Max
T_{DXD}	DX inputs to DMUX output	0.32	0.33	0.40	0.52	ns, Max
Sequential Delays						
T_{CKO}	Clock to AQ – DQ outputs	0.26	0.27	0.32	0.40	ns, Max
T_{SHCKO}	Clock to AMUX – DMUX outputs	0.32	0.32	0.39	0.46	ns, Max
Setup and Hold Times of CLB Flip-Flops Before/After Clock CLK						
T_{AS}/T_{AH}	A_N – D_N input to CLK on A – D Flip Flops	0.01/0.12	0.02/0.13	0.03/0.18	0.02/0.18	ns, Min
T_{DICK}/T_{CKDI}	A_X – D_X input to CLK on A – D Flip Flops	0.04/0.14	0.04/0.14	0.05/0.20	0.05/0.21	ns, Min
	A_X – D_X input through MUXs and/or carry logic to CLK on A – D Flip Flops	0.36/0.10	0.37/0.11	0.46/0.16	0.56/0.15	ns, Min
T_{CECK_CLB}/ T_{CKCE_CLB}	CE input to CLK on A – D Flip Flops	0.19/0.05	0.20/0.05	0.25/0.05	0.24/0.04	ns, Min
T_{SRCK}/T_{CKSR}	SR input to CLK on A – D Flip Flops	0.30/0.05	0.31/0.07	0.37/0.09	0.48/0.05	ns, Min
Set/Reset						
T_{SRMIN}	SR input minimum pulse width	0.52	0.78	1.04	0.95	ns, Min
T_{RQ}	Delay from SR input to AQ – DQ flip-flops	0.38	0.38	0.46	0.59	ns, Max
T_{CEO}	Delay from CE input to AQ – DQ flip-flops	0.34	0.35	0.43	0.54	ns, Max
F_{TOG}	Toggle frequency (for export control)	1818	1818	1818	1286	MHz

Block RAM and FIFO Switching Characteristics

Table 31: **Block RAM and FIFO Switching Characteristics**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
Block RAM and FIFO Clock-to-Out Delays						
T_{RCKO_DO} and $T_{RCKO\_DO\_REG}$(1)	Clock CLK to DOUT output (without output register)(2)(3)	1.57	1.80	2.08	2.44	ns, Max
	Clock CLK to DOUT output (with output register)(4)(5)	0.54	0.63	0.75	0.86	ns, Max
$T_{RCKO\_DO\_ECC}$ and $T_{RCKO\_DO\_ECC\_REG}$	Clock CLK to DOUT output with ECC (without output register)(2)(3)	2.35	2.58	3.26	4.49	ns, Max
	Clock CLK to DOUT output with ECC (with output register)(4)(5)	0.62	0.69	0.80	0.94	ns, Max
$T_{RCKO\_DO\_CASCOUT}$ and $T_{RCKO\_DO\_CASCOUT\_REG}$	Clock CLK to DOUT output with Cascade (without output register)(2)	2.21	2.45	2.80	3.19	ns, Max
	Clock CLK to DOUT output with Cascade (with output register)(4)	0.98	1.08	1.24	1.32	ns, Max
T_{RCKO_FLAGS}	Clock CLK to FIFO flags outputs(6)	0.65	0.74	0.89	0.97	ns, Max
$T_{RCKO\_POINTERS}$	Clock CLK to FIFO pointers outputs(7)	0.79	0.87	0.98	1.10	ns, Max
$T_{RCKO\_PARITY\_ECC}$	Clock CLK to ECCPARITY in ECC encode only mode	0.66	0.72	0.80	0.93	ns, Max
$T_{RCKO\_SDBIT\_ECC}$ and $T_{RCKO\_SDBIT\_ECC\_REG}$	Clock CLK to BITERR (without output register)	2.17	2.38	3.01	4.15	ns, Max
	Clock CLK to BITERR (with output register)	0.57	0.65	0.76	0.89	ns, Max
$T_{RCKO\_RDADDR\_ECC}$ and $T_{RCKO\_RDADDR\_ECC\_REG}$	Clock CLK to RDADDR output with ECC (without output register)	0.64	0.74	0.90	0.98	ns, Max
	Clock CLK to RDADDR output with ECC (with output register)	0.71	0.79	0.92	1.10	ns, Max
Setup and Hold Times Before/After Clock CLK						
T_{RCCK_ADDRA}/T_{RCKC_ADDRA}	ADDR inputs(8)	0.38/0.27	0.42/0.28	0.48/0.31	0.65/0.38	ns, Min
$T_{RDCK\_DI\_WF\_NC}$/ $T_{RCKD\_DI\_WF\_NC}$	Data input setup/hold time when block RAM is configured in WRITE_FIRST or NO_CHANGE mode(9)	0.49/0.51	0.55/0.53	0.63/0.57	0.78/0.64	ns, Min
$T_{RDCK\_DI\_RF}$/$T_{RCKD\_DI\_RF}$	Data input setup/hold time when block RAM is configured in READ_FIRST mode(9)	0.17/0.25	0.19/0.29	0.21/0.35	0.25/0.32	ns, Min
$T_{RDCK\_DI\_ECC}$/ $T_{RCKD\_DI\_ECC}$	DIN inputs with block RAM ECC in standard mode(9)	0.42/0.37	0.47/0.39	0.53/0.43	0.66/0.46	ns, Min
$T_{RDCK\_DI\_ECCW}$/ $T_{RCKD\_DI\_ECCW}$	DIN inputs with block RAM ECC encode only(9)	0.79/0.37	0.87/0.39	0.99/0.43	1.17/0.41	ns, Min
$T_{RDCK\_DI\_ECC\_FIFO}$/ $T_{RCKD\_DI\_ECC\_FIFO}$	DIN inputs with FIFO ECC in standard mode(9)	0.89/0.47	0.98/0.50	1.12/0.54	1.32/0.65	ns, Min
$T_{RCCK\_INJECTBITERR}$/ $T_{RCKC\_INJECTBITERR}$	Inject single/double bit error in ECC mode	0.49/0.30	0.55/0.31	0.63/0.34	0.78/0.41	ns, Min
T_{RCCK_EN}/T_{RCKC_EN}	Block RAM Enable (EN) input	0.30/0.17	0.33/0.18	0.38/0.20	0.48/0.22	ns, Min
T_{RCCK_REGCE}/T_{RCKC_REGCE}	CE input of output register	0.21/0.13	0.25/0.13	0.31/0.14	0.34/0.16	ns, Min
T_{RCCK_RSTREG}/T_{RCKC_RSTREG}	Synchronous RSTREG input	0.25/0.06	0.27/0.06	0.29/0.06	0.35/0.06	ns, Min

Table 32: **DSP48E1 Switching Characteristics *(Cont'd)***

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
Setup and Hold Times of the RST Pins						
$T_{\text{DSPDCK\_\{RSTA; RSTB\}\_\{AREG; BREG\}}}$/ $T_{\text{DSPCKD\_\{RSTA; RSTB\}\_\{AREG; BREG\}}}$	{RSTA, RSTB} input to {A, B} register CLK	0.34/ 0.10	0.39/ 0.11	0.47/ 0.13	0.53/ 0.34	ns
$T_{\text{DSPDCK\_RSTC\_CREG}}$/ $T_{\text{DSPCKD\_RSTC\_CREG}}$	RSTC input to C register CLK	0.06/ 0.22	0.07/ 0.24	0.08/ 0.26	0.08/ 0.31	ns
$T_{\text{DSPDCK\_RSTD\_DREG}}$/ $T_{\text{DSPCKD\_RSTD\_DREG}}$	RSTD input to D register CLK	0.37/ 0.06	0.42/ 0.06	0.50/ 0.07	0.57/ 0.07	ns
$T_{\text{DSPDCK\_RSTM\_MREG}}$/ $T_{\text{DSPCKD\_RSTM\_MREG}}$	RSTM input to M register CLK	0.18/ 0.18	0.20/ 0.21	0.23/ 0.24	0.24/ 0.29	ns
$T_{\text{DSPDCK\_RSTP\_PREG}}$/ $T_{\text{DSPCKD\_RSTP\_PREG}}$	RSTP input to P register CLK	0.24/ 0.01	0.26/ 0.01	0.30/ 0.01	0.37/ 0.00	ns
Combinatorial Delays from Input Pins to Output Pins						
$T_{\text{DSPDO\_A\_CARRYOUT\_MULT}}$	A input to CARRYOUT output using multiplier	3.21	3.69	4.39	5.60	ns
$T_{\text{DSPDO\_D\_P\_MULT}}$	D input to P output using multiplier	3.15	3.61	4.30	5.44	ns
$T_{\text{DSPDO\_A\_P}}$	A input to P output not using multiplier	1.30	1.48	1.76	2.10	ns
$T_{\text{DSPDO\_C\_P}}$	C input to P output	1.13	1.30	1.55	1.84	ns
Combinatorial Delays from Input Pins to Cascading Output Pins						
$T_{\text{DSPDO\_\{A; B\}\_\{ACOUT; BCOUT\}}}$	{A, B} input to {ACOUT, BCOUT} output	0.47	0.53	0.63	0.75	ns
$T_{\text{DSPDO\_\{A, B\}\_CARRYCASCOUT\_MULT}}$	{A, B} input to CARRYCASCOUT output using multiplier	3.44	3.94	4.69	5.96	ns
$T_{\text{DSPDO\_D\_CARRYCASCOUT\_MULT}}$	D input to CARRYCASCOUT output using multiplier	3.36	3.85	4.58	5.77	ns
$T_{\text{DSPDO\_\{A, B\}\_CARRYCASCOUT}}$	{A, B} input to CARRYCASCOUT output not using multiplier	1.50	1.72	2.04	2.44	ns
$T_{\text{DSPDO\_C\_CARRYCASCOUT}}$	C input to CARRYCASCOUT output	1.34	1.53	1.83	2.18	ns
Combinatorial Delays from Cascading Input Pins to All Output Pins						
$T_{\text{DSPDO\_ACIN\_P\_MULT}}$	ACIN input to P output using multiplier	3.09	3.55	4.24	5.42	ns
$T_{\text{DSPDO\_ACIN\_P}}$	ACIN input to P output not using multiplier	1.16	1.33	1.59	2.07	ns
$T_{\text{DSPDO\_ACIN\_ACOUT}}$	ACIN input to ACOUT output	0.32	0.37	0.45	0.53	ns
$T_{\text{DSPDO\_ACIN\_CARRYCASCOUT\_MULT}}$	ACIN input to CARRYCASCOUT output using multiplier	3.30	3.79	4.52	5.76	ns
$T_{\text{DSPDO\_ACIN\_CARRYCASCOUT}}$	ACIN input to CARRYCASCOUT output not using multiplier	1.37	1.57	1.87	2.40	ns
$T_{\text{DSPDO\_PCIN\_P}}$	PCIN input to P output	0.94	1.08	1.29	1.54	ns
$T_{\text{DSPDO\_PCIN\_CARRYCASCOUT}}$	PCIN input to CARRYCASCOUT output	1.15	1.32	1.57	1.88	ns
Clock to Outs from Output Register Clock to Output Pins						
$T_{\text{DSPCKO\_P\_PREG}}$	CLK PREG to P output	0.33	0.35	0.39	0.45	ns
$T_{\text{DSPCKO\_CARRYCASCOUT\_PREG}}$	CLK PREG to CARRYCASCOUT output	0.44	0.50	0.59	0.71	ns

Clock Buffers and Networks

Table 33: **Global Clock Switching Characteristics (Including BUFGCTRL)**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
T_{BCCCK_CE}/T_{BCCKC_CE}(1)	CE pins Setup/Hold	0.12/0.30	0.14/0.38	0.26/0.38	0.23/0.40	ns
T_{BCCCK_S}/T_{BCCKC_S}(1)	S pins Setup/Hold	0.12/0.30	0.14/0.38	0.26/0.38	0.23/0.40	ns
T_{BCCKO_O}(2)	BUFGCTRL delay from I0/I1 to O	0.08	0.10	0.12	0.10	ns
Maximum Frequency						
F_{MAX_BUFG}	Global clock tree (BUFG)	741.00	710.00	625.00	560.00	MHz

Notes:

1. T_{BCCCK_CE} and T_{BCCKC_CE} must be satisfied to assure glitch-free operation of the global clock when switching between clocks. These parameters do not apply to the BUFGMUX primitive that assures glitch-free operation. The other global clock setup and hold times are optional; only needing to be satisfied if device operation requires simulation matches on a cycle-for-cycle basis when switching between clocks.
2. T_{BGCKO_O} (BUFG delay from I0 to O) values are the same as T_{BCCKO_O} values.

Table 34: **Input/Output Clock Switching Characteristics (BUFIO)**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
T_{BIOCKO_O}	Clock to out delay from I to O	1.04	1.14	1.32	1.48	ns
Maximum Frequency						
F_{MAX_BUFIO}	I/O clock tree (BUFIO)	800.00	800.00	710.00	710.00	MHz

Table 35: **Regional Clock Buffer Switching Characteristics (BUFR)**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
T_{BRCKO_O}	Clock to out delay from I to O	0.60	0.65	0.77	1.06	ns
$T_{BRCKO\_O\_BYP}$	Clock to out delay from I to O with Divide Bypass attribute set	0.30	0.32	0.38	0.57	ns
T_{BRDO_O}	Propagation delay from CLR to O	0.71	0.75	0.96	0.93	ns
Maximum Frequency						
F_{MAX_BUFR}(1)	Regional clock tree (BUFR)	600.00	540.00	450.00	450.00	MHz

Notes:

1. The maximum input frequency to the BUFR is the BUFIO F_{MAX} frequency.

Device Pin-to-Pin Output Parameter Guidelines

All devices are 100% functionally tested. Values are expressed in nanoseconds unless otherwise noted.

Table 40: **Clock-Capable Clock Input to Output Delay Without MMCM/PLL (Near Clock Region)**

Symbol	Description	Device	Speed Grade				Units
			1.0V			0.9V	
			-3	-2/-2L	-1	-2L	
SSTL15 Clock-Capable Clock Input to Output Delay using Output Flip-Flop, Fast Slew Rate, *without* MMCM/PLL.							
T_{ICKOF}	Clock-capable clock input and OUTFF *without* MMCM/PLL (near clock region)	XC7K70T	4.98	5.49	6.17	7.04	ns
		XC7K160T	5.23	5.77	6.48	7.38	ns
		XC7K325T	5.72	6.31	7.09	8.07	ns
		XC7K355T	5.34	5.87	6.57	7.51	ns
		XC7K410T	5.84	6.44	7.22	8.21	ns
		XC7K420T	5.50	6.04	6.77	7.73	ns
		XC7K480T	5.50	6.04	6.77	7.73	ns

Notes:

1. Listed above are representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible IOB and CLB flip-flops are clocked by the global clock net.

Table 41: **Clock-Capable Clock Input to Output Delay Without MMCM/PLL (Far Clock Region)**

Symbol	Description	Device	Speed Grade				Units
			1.0V			0.9V	
			-3	-2/-2L	-1	-2L	
SSTL15 Clock-Capable Clock Input to Output Delay using Output Flip-Flop, Fast Slew Rate, *without* MMCM/PLL.							
$T_{ICKOFFAR}$	Clock-capable clock input and OUTFF *without* MMCM/PLL (far clock region)	XC7K70T	5.29	5.83	6.55	7.47	ns
		XC7K160T	5.84	6.45	7.24	8.24	ns
		XC7K325T	6.33	6.99	7.84	8.92	ns
		XC7K355T	5.95	6.55	7.32	8.36	ns
		XC7K410T	6.45	7.12	7.97	9.07	ns
		XC7K420T	6.41	7.06	7.90	9.01	ns
		XC7K480T	6.41	7.06	7.90	9.01	ns

Notes:

1. Listed above are representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible IOB and CLB flip-flops are clocked by the global clock net.

GTX Transceiver Specifications

GTX Transceiver DC Input and Output Levels

Table 51 summarizes the DC output specifications of the GTX transceivers in Kintex-7 FPGAs. Consult UG476: *7 Series FPGAs GTX/GTH Transceiver User Guide* for further details.

Table 51: **GTX Transceiver DC Specifications**

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
DV_{PPOUT}	Differential peak-to-peak output voltage[1]	Transmitter output swing is set to maximum setting	–	–	1000	mV
$V_{CMOUTDC}$	DC common mode output voltage.	Equation based	$V_{MGTAVTT} – DV_{PPOUT}/4$			mV
R_{OUT}	Differential output resistance		–	100	–	Ω
T_{OSKEW}	Transmitter output pair (TXP and TXN) intra-pair skew		–	2	12	ps
DV_{PPIN}	Differential peak-to-peak input voltage (external AC coupled)	>10.3125 Gb/s	150	–	1250	mV
		6.6 Gb/s to 10.3125 Gb/s	150	–	1250	mV
		≤ 6.6 Gb/s	150	–	2000	mV
V_{IN}	Absolute input voltage	DC coupled $V_{MGTAVTT} = 1.2V$	–200	–	$V_{MGTAVTT}$	mV
V_{CMIN}	Common mode input voltage	DC coupled $V_{MGTAVTT} = 1.2V$	–	2/3 $V_{MGTAVTT}$	–	mV
R_{IN}	Differential input resistance		–	100	–	Ω
C_{EXT}	Recommended external AC coupling capacitor[2]		–	100	–	nF

Notes:

1. The output swing and preemphasis levels are programmable using the attributes discussed in UG476: *7 Series FPGAs GTX/GTH Transceiver User Guide* and can result in values lower than reported in this table.
2. Other values can be used as appropriate to conform to specific protocols and standards.

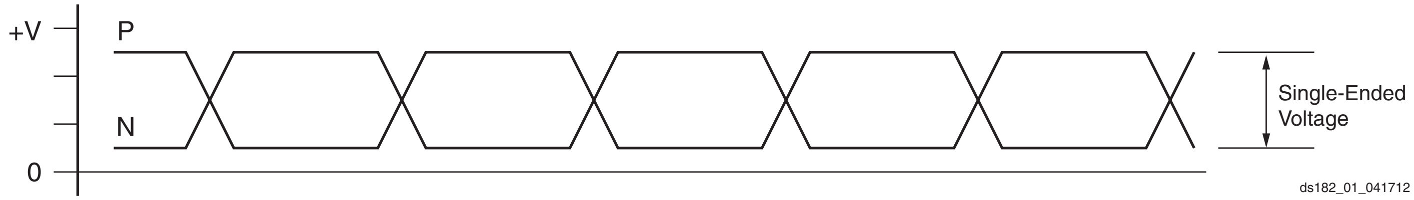

Figure 1: **Single-Ended Peak-to-Peak Voltage**

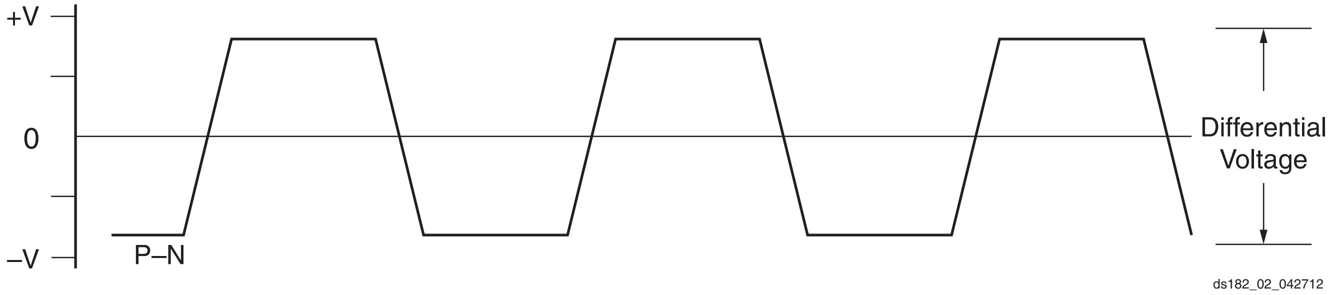

Figure 2: **Differential Peak-to-Peak Voltage**

Table 52 summarizes the DC specifications of the clock input of the GTX transceiver. Consult UG476: *7 Series FPGAs GTX/GTH Transceiver User Guide* for further details.

Table 52: **GTX Transceiver Clock DC Input Level Specification**

Symbol	DC Parameter	Min	Typ	Max	Units
V_{IDIFF}	Differential peak-to-peak input voltage	250	–	2000	mV
R_{IN}	Differential input resistance	–	100	–	Ω
C_{EXT}	Required external AC coupling capacitor	–	100	–	nF

GTX Transceiver Switching Characteristics

Consult UG476: *7 Series FPGAs GTX/GTH Transceiver User Guide* for further information.

Table 53: **GTX Transceiver Performance**

Symbol	Description	Output Divider	Speed Grade								Units
			1.0V						0.9V		
			-3		-2/-2L		-1(1)		-2L(2)		
			Package Type								
			FF	FB	FF	FB	FF	FB	FF	FB	
F_{GTXMAX}(3)	Maximum GTX transceiver data rate		12.5	6.6	10.3125	6.6	8.0	6.6	6.6	6.6	Gb/s
F_{GTXMIN}(3)	Minimum GTX transceiver data rate		0.500	0.500	0.500	0.500	0.500	0.500	0.500	0.500	Gb/s
$F_{GTXCRANGE}$	CPLL line rate range	1	3.2–6.6								Gb/s
		2	1.6–3.3								Gb/s
		4	0.8–1.65								Gb/s
		8	0.5–0.825								Gb/s
		16	N/A								Gb/s
$F_{GTXQRANGE1}$	QPLL line rate range 1	1	5.93–8.0	5.93–6.6	5.93–8.0	5.93–6.6	5.93–8.0	5.93–6.6	5.93–6.6		Gb/s
		2	2.965–4.0		2.965–4.0		2.965–4.0		2.965–3.3		Gb/s
		4	1.4825–2.0		1.4825–2.0		1.4825–2.0		1.4825–1.65		Gb/s
		8	0.74125–1.0		0.74125–1.0		0.74125–1.0		0.74125–0.825		Gb/s
		16	N/A		N/A		N/A		N/A		Gb/s
$F_{GTXQRANGE2}$	QPLL line rate range 2(4)	1	9.8–12.5	N/A	9.8–10.3125	N/A	N/A		N/A		Gb/s
		2	4.9–6.25		4.9–5.15625		N/A		N/A		Gb/s
		4	2.45–3.125		2.45–2.578125		N/A		N/A		Gb/s
		8	1.225–1.5625		1.225–1.2890625		N/A		N/A		Gb/s
		16	0.6125–0.78125		0.6125–0.64453125		N/A		N/A		Gb/s
$F_{GCPLLRANGE}$	GTX transceiver CPLL frequency range		1.6–3.3		1.6–3.3		1.6–3.3		1.6–3.3		GHz
$F_{GQPLLRANGE1}$	GTX transceiver QPLL frequency range 1		5.93–8.0		5.93–8.0		5.93–8.0		5.93–6.6		GHz

Table 56: **GTX Transceiver PLL /Lock Time Adaptation**

Symbol	Description	Conditions	All Speed Grades			Units
			Min	Typ	Max	
T_{LOCK}	Initial PLL lock		–	–	1	ms
T_{DLOCK}	Clock recovery phase acquisition and adaptation time for decision feedback equalizer (DFE).	After the PLL is locked to the reference clock, this is the time it takes to lock the clock data recovery (CDR) to the data present at the input.	–	50,000	37 x10^6	UI
	Clock recovery phase acquisition and adaptation time for low-power mode (LPM) when the DFE is disabled.		–	50,000	2.3 x10^6	UI

Table 57: **GTX Transceiver User Clock Switching Characteristics(1)(2)**

Symbol	Description	Conditions	Speed Grade				Units
			1.0V			0.9V	
			-3(3)	-2/-2L(3)	-1(4)	-2L(5)	
F_{TXOUT}	TXOUTCLK maximum frequency		412.54	412.54	312.50	237.53	MHz
F_{RXOUT}	RXOUTCLK maximum frequency		412.54	412.54	312.50	237.53	MHz
F_{TXIN}	TXUSRCLK maximum frequency	16-bit data path	412.54	412.54	312.50	237.53	MHz
		32-bit data path	391.08	322.37	250.00	206.27	MHz
F_{RXIN}	RXUSRCLK maximum frequency	16-bit data path	412.54	412.54	312.50	237.53	MHz
		32-bit data path	391.08	322.37	250.00	206.27	MHz
F_{TXIN2}	TXUSRCLK2 maximum frequency	16-bit data path	412.54	412.54	312.50	237.53	MHz
		32-bit data path	391.08	322.37	250.00	206.27	MHz
		64-bit data path	195.54	161.19	125.00	103.14	MHz
F_{RXIN2}	RXUSRCLK2 maximum frequency	16-bit data path	412.54	412.54	312.50	237.53	MHz
		32-bit data path	391.08	322.37	250.00	206.27	MHz
		64-bit data path	195.54	161.19	125.00	103.14	MHz

Notes:

1. Clocking must be implemented as described in UG476: *7 Series FPGAs GTX/GTH Transceiver User Guide*.
2. These frequencies are not supported for all possible transceiver configurations.
3. For speed grades -3, -2, -2L (1.0V), a 16-bit data path can only be used for speeds less than 6.6 Gb/s.
4. For speed grade -1, a 16-bit data path can only be used for speeds less than 5.0 Gb/s.
5. For speed grade -2L (0.9V), a 16-bit data path can only be used for speeds less than 3.8 Gb/s.

Table 58: **GTX Transceiver Transmitter Switching Characteristics**

Symbol	Description	Condition	Min	Typ	Max	Units
F_{GTXTX}	Serial data rate range		0.500	–	F_{GTXMAX}	Gb/s
T_{RTX}	TX Rise time	20%–80%	–	40	–	ps
T_{FTX}	TX Fall time	80%–20%	–	40	–	ps
T_{LLSKEW}	TX lane-to-lane skew(1)		–	–	500	ps
$V_{TXOOBVDPP}$	Electrical idle amplitude		–	–	15	mV
$T_{TXOOBTRANSITION}$	Electrical idle transition time		–	–	140	ns
$TJ_{12.5}$	Total Jitter(2)(4)	12.5 Gb/s	–	–	0.28	UI
$DJ_{12.5}$	Deterministic Jitter(2)(4)		–	–	0.17	UI
$TJ_{11.18}$	Total Jitter(2)(4)	11.18 Gb/s	–	–	0.28	UI
$DJ_{11.18}$	Deterministic Jitter(2)(4)		–	–	0.17	UI

GTX Transceiver Protocol Jitter Characteristics

For Table 60 through Table 65, the UG476: *7 Series FPGAs GTX/GTH Transceiver User Guide* contains recommended settings for optimal usage of protocol specific characteristics.

Table 60: **Gigabit Ethernet Protocol Characteristics**

Description	Line Rate (Mb/s)	Min	Max	Units
Gigabit Ethernet Transmitter Jitter Generation				
Total transmitter jitter (T_TJ)	1250	–	0.24	UI
Gigabit Ethernet Receiver High Frequency Jitter Tolerance				
Total receiver jitter tolerance	1250	0.749	–	UI

Table 61: **XAUI Protocol Characteristics**

Description	Line Rate (Mb/s)	Min	Max	Units
XAUI Transmitter Jitter Generation				
Total transmitter jitter (T_TJ)	3125	–	0.35	UI
XAUI Receiver High Frequency Jitter Tolerance				
Total receiver jitter tolerance	3125	0.65	–	UI

Table 62: **PCI Express Protocol Characteristics(1)**

Standard	Description		Line Rate (Mb/s)	Min	Max	Units
PCI Express Transmitter Jitter Generation						
PCI Express Gen 1	Total transmitter jitter		2500	–	0.25	UI
PCI Express Gen 2	Total transmitter jitter		5000	–	0.25	UI
PCI Express Gen 3(2)	Total transmitter jitter uncorrelated		8000	–	31.25	ps
	Deterministic transmitter jitter uncorrelated			–	12	ps
PCI Express Receiver High Frequency Jitter Tolerance						
PCI Express Gen 1	Total receiver jitter tolerance		2500	0.65	–	UI
PCI Express Gen 2(3)	Receiver inherent timing error		5000	0.40	–	UI
	Receiver inherent deterministic timing error			0.30	–	UI
PCI Express Gen 3(2)	Receiver sinusoidal jitter tolerance	0.03 MHz–1.0 MHz	8000	1.00	–	UI
		1.0 MHz–10 MHz		Note 4	–	UI
		10 MHz–100 MHz		0.10	–	UI

Notes:

1. Tested per card electromechanical (CEM) methodology.
2. PCI-SIG 3.0 certification and compliance test boards are currently not available.
3. Using common REFCLK.
4. Between 1 MHz and 10 MHz the minimum sinusoidal jitter roll-off with a slope of 20dB/decade.

XADC Specifications

Table 67: **XADC Specifications**

Parameter	Symbol	Comments/Conditions	Min	Typ	Max	Units
V_{CCADC} = 1.8V ± 5%, V_{REFP} = 1.25V, V_{REFN} = 0V, ADCCLK = 26 MHz, T_j = –40°C to 100°C, Typical values at T_j=+40°C						
ADC Accuracy(1)						
Resolution			12	–	–	Bits
Integral Nonlinearity(2)	INL		–	–	±3	LSBs
Differential Nonlinearity	DNL	No missing codes, guaranteed monotonic	–	–	±1	LSBs
Offset Error		Offset calibration enabled	–	–	±6	LSBs
Gain Error		Gain calibration disabled	–	–	±0.5	%
Offset Matching		Offset calibration enabled	–	–	4	LSBs
Gain Matching		Gain calibration disabled	–	–	0.3	%
Sample Rate			0.1	–	1	MS/s
Signal to Noise Ratio(2)	SNR	F_{SAMPLE} = 500KS/s, F_{IN} = 20KHz	60	–	–	dB
RMS Code Noise		External 1.25V reference	–	–	2	LSBs
		On-chip reference	–	3	–	LSBs
Total Harmonic Distortion(2)	THD	F_{SAMPLE} = 500KS/s, F_{IN} = 20KHz	–	70	–	dB
ADC Accuracy at Extended Temperatures (-55°C to 125°C)						
Resolution			10	–	–	Bits
Integral Nonlinearity(2)	INL		–	–	±1	LSB (at 10 bits)
Differential Nonlinearity	DNL	No missing codes, guaranteed monotonic	–	–	±1	
Analog Inputs(3)						
ADC Input Ranges		Unipolar operation	0	–	1	V
		Bipolar operation	–0.5	–	+0.5	V
		Unipolar common mode range (FS input)	0	–	+0.5	V
		Bipolar common mode range (FS input)	+0.5	–	+0.6	V
Maximum External Channel Input Ranges		Adjacent channels set within these ranges should not corrupt measurements on adjacent channels	–0.1	–	V_{CCADC}	V
Auxiliary Channel Full Resolution Bandwidth	FRBW		250	–	–	KHz
On-Chip Sensors						
Temperature Sensor Error		T_j = –40°C to 100°C.	–	–	±4	°C
		T_j = –55°C to +125°C	–	–	±6	°C
Supply Sensor Error		Measurement range of V_{CCAUX} 1.8V ±5% T_j = –40°C to +100°C	–	–	±1	%
		Measurement range of V_{CCAUX} 1.8V ±5% T_j = –55°C to +125°C	–	–	±2	%
Conversion Rate(4)						
Conversion Time - Continuous	t_{CONV}	Number of ADCCLK cycles	26	–	32	Cycles
Conversion Time - Event	t_{CONV}	Number of CLK cycles	–	–	21	Cycles
DRP Clock Frequency	DCLK	DRP clock frequency	8	–	250	MHz
ADC Clock Frequency	ADCCLK	Derived from DCLK	1	–	26	MHz
DCLK Duty Cycle			40	–	60	%

Revision History

The following table shows the revision history for this document:

Date	Version	Description
03/01/11	1.0	Initial Xilinx release.
04/01/11	1.1	Added the XC7K355T, XC7K420T, and XC7K480T devices throughout data sheet. Added the extended temperature range discussion to page 1. Updated V_{CCAUX_IO} in Table 2. Edits to clarify Power-On/Off Power Supply Sequencing power sequencing discussion. Added I_{CCAUX_IO} and I_{CCBRAM} to Table 6 and Table 7. Updated MMCM_F_{INDUTY} and added $F_{INJITTER}$, $T_{OUTJITTER}$, $T_{EXTFDVAR}$, and Note 3 to Table 38. Removed the SBG324 package from Table 50. Updated the Notice of Disclaimer.
10/04/11	1.2	Replaced -1L with -2L throughout this data sheet. Updated Min/Max values and removed Note 5 from Table 2. Clarified Power-On/Off Power Supply Sequencing power sequencing discussion including adding $T_{VCCO2VCCAUX}$ to Table 8. Updated V_{ICM} in Table 12 and Table 13. Added Note 1 to table 12. Updated Table 69 including adding Note 1. Added *Absolute Maximum Ratings for GTX Transceivers*. Revised the reference clock maximum frequency (F_{GCLK}) in Table 55. Added Table 57. Added LVTTL and removed SSTL135_II and SSTL15_II specifications from Table 19. Removed HSTL_III from Table 20. Removed the *I/O Standard Adjustment Measurement Methodology* section. Use IBIS for more accurate information and measurements. Updated $T_{IDELAYPAT\_JIT}$ in Table 26. Added T_{AS}/T_{AH} to Table 28. Added $T_{RDCK\_DI\_WF\_NC}/T_{RCKD\_DI\_WF\_NC}$ and $T_{RDCK\_DI\_RF}/T_{RCKD\_DI\_RF}$ to Table 31. Completely updated Table 68. Updated the AC Switching Characteristics in Table 19, Table 20, Table 21, Table 22, Table 23, Table 24, Table 26 through Table 38, Table 40 though Table 37, and Table 67.
11/03/11	1.3	Revised the V_{OCM} specification in Table 12. Updated the AC Switching Characteristics based upon the ISE 13.3 v1.02 speed specification throughout document including Table 19 and Table 20. Added MMCM_$T_{FBDELAY}$ while adding MMCM_ to the symbol names of a few specifications in Table 38 and PLL to the symbol names in Table 39. In Table 40 through Table 47, updated the pin-to-pin descriptions with the SSTL15 standard. Updated units in Table 49.
02/13/12	1.4	Updated summary description on page 1. In Table 2, revised V_{CCO} for the 3.3V HR I/O banks and updated T_j. Added typical values to Table 3. Updated the notes in Table 6. Added MGTAVCC, MGTAVTT, and MGTVCCAUX power supply ramp times to Table 8. Rearranged Table 9, added Mobile_DDR, HSTL_I_18, HSTL_II_18, HSUL_12, SSTL135_R, SSTL15_R, and SSTL12 and removed DIFF_SSTL135, DIFF_SSTL18_I, DIFF_SSTL18_II, DIFF_HSTL_I, and DIFF_HSTL_II. Added Table 10 and Table 11. Revised the specifications in Table 12 and Table 13. Updated the eFUSE Programming Conditions section and removed the endurance table. Added the IO_FIFO Switching Characteristics table. Revised I_{CCADC} and updated Note 1 in Table 67. Revised DDR LVDS transmitter data width in Table 16. Updated the AC Switching Characteristics based upon the ISE 13.4 v1.03 speed specification throughout document. Removed notes from Table 28 as they are no longer applicable. Updated specifications in Table 68. Updated Note 1 in Table 37. In the GTX Transceiver DC Input and Output Levels section: Revised V_{IN}, and added I_{DCIN} and I_{DCOUT} to Table 51. Added Note 4 to Table 53. In Table 55, revised F_{GCLK}, removed T_{PHASE}, and added T_{DLOCK}. Revised specifications and added Note 2 to Table 57. Added Table 58 and Table 59 along with GTX Transceiver Protocol Jitter Characteristics in Table 60 through Table 65.
05/23/12	1.5	Reorganized entire data sheet including adding Table 44 and Table 48. Updated T_{SOL} in Table 1. Updated I_{BATT} and added R_{IN_TERM} to Table 3. Added values to Table 6 and Table 7. Updated Power-On/Off Power Supply Sequencing, page 6 with regards to GTX transceivers. Updated many parameters in Table 9 including SSTL135 and SSTL135_R. Removed V_{OX} column and added DIFF_HSUL_12 to Table 11. Updated V_{OL} in Table 12. Updated Table 16 and removed notes 2 and 3. Updated Table 17. Updated the AC Switching Characteristics based upon the ISE 14.1 v1.04 for the -3, -2, -2L (1.0V), -1, and -2L (0.9V) speed specifications throughout the document. In Table 31, updated Reset Delays section including Note 10 and Note 11. Added data for T_{LOCK} and T_{DLOCK} in Table 55. Updated many of the XADC specifications in Table 67 and added Note 2. Updated and moved *Dynamic Reconfiguration Port (DRP) for MMCM Before and After DCLK* section from Table 68 to Table 38 and Table 39.